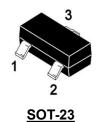


PNP Switching Transistor

> Features

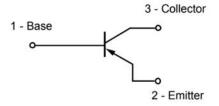
VCB	VCE	VEB	IC
-80V	-60V	-5V	-1A

Pin configuration



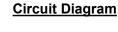
> Description

The PNP Transistor is designed for use in linear and switching applications. The device is housed in the SOT-23 package, which is designed for telephony and professional communication equipment.



> Applications

- General purpose switching and amplification
- Telephony and professional communication equipment



> Ordering Information

Device	Package	Shipping
SSCP591GS6	SOT-23	3000/Reel





> Absolute Maximum Ratings($T_A = 25^{\circ}C$ unless otherwise noted)

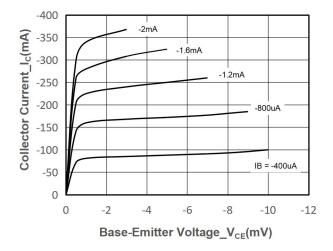
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector- Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current-Continuous	lc	-1	A
Collector Power Dissipation	Pc	250	mW
Junction Temperature	TJ	-55 to 150	°C
Storage Temperature	T _{STG}	-55 to 150	°C

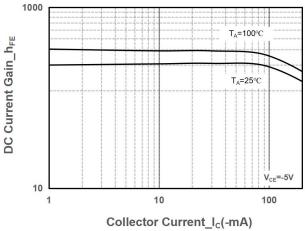
> Electrical Characteristics ($T_A = 25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	ВV _{сво}	$I_{\rm C}$ = -100uA, $I_{\rm E}$ = 0	-80			V
Collector-emitter Breakdown Voltage	BV _{CEO}	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$	-60			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E = -100uA, I _C = 0	-5			V
Collector Cutoff Current	I _{СВО}	$V_{CB} = -60V, I_E = 0$			-0.1	μA
Emitter Cutoff Current	I _{EBO}	$V_{EB} = -4V, I_{C} = 0$			-0.1	μA
	h _{FE1}	V _{CE} = -5V, I _C = -1mA	100			
DC Current Gain	h _{FE2}	V _{CE} = -5V, I _C = -500mA	100		300	
	h _{FE3}	V _{CE} = -5V, I _C = -1A	80			
	h _{FE4}	V _{CE} = -5V, I _C = -2A	15			
Collector Emitter Seturation Voltage	V _{CE (sat)1}	I _C = -500mA, I _B = -50mA			-0.3	V
Collector-Emitter Saturation Voltage	V _{CE} (sat)2	I _C = -1A, I _B = -100mA			-0.6	V
Base-Emitter Saturation Base-Emitter	V _{BE (sat)}	I _B = -1A, I _C = -1A			-1.2	V
Base-Emitter Voltage	V _{BE}	V _{CE} = -5V,I _C = -1A			-1	V
Transition frequency	fT	V _{CE} = -10V, I _C = -50mA f = 100MHz	150			MHz
Collector output capacitance	Cob	V _{CB} = -10V f = 1MHz			10	pF

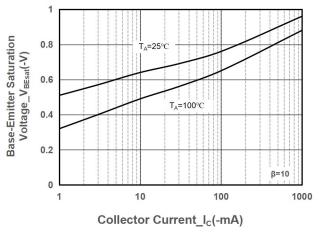


> Typical Performance Characteristics ($T_A = 25^{\circ}C$ unless otherwise noted)

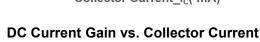


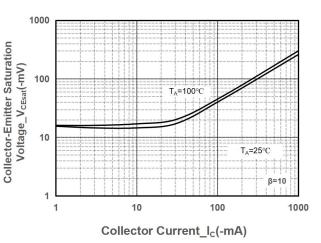


Collector Current vs. Base-Emitter Voltage

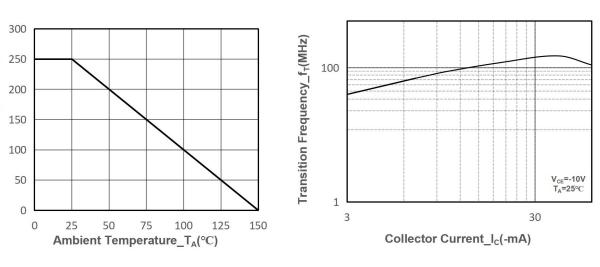


V_{BE (sat)} vs. Collector Current





V_{CE (sat)} vs. Collector Current



Power derating vs. Ambient temperature

Transition Frequency vs. Collector Current

Dissipation_P_c(mW)

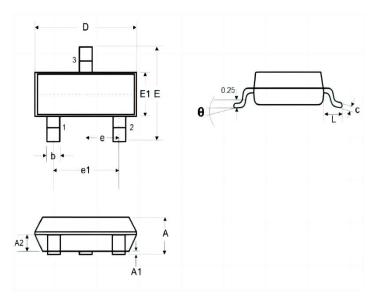
Collector Power

3/5



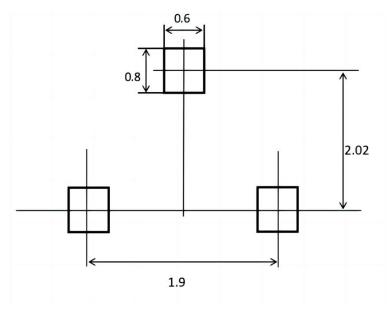
> Package Information

<u>SOT-23</u>



DIM	Millimeters			
	Min.	Тур.	Max.	
Α	0.89	-	1.12	
A1	0.01	-	0.10	
A2	0.88	0.95	1.02	
b	0.30	-	0.51	
C	0.08	-	0.18	
D	2.800	2.90	3.000	
E	2.10	2.37	2.64	
E1	1.20	1.30	1.40	
е	0.95			
e1	1.80	-	2.00	
L	0.40	0.50	0.60	
L1	0.30		0.50	
θ	0°	-	8°	

Recommended Pad outline (Unit: mm)





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